



DEPOSITION SYSTEMS FOR COMPOUND SEMICONDUCTORS

AIX G5+ Planetary Reactor® for GaN on 200 mm Si

AIXTRON
Our technology. Your future.

Single wafer performance with batch reactor benefits

AIX G5+ MOCVD System

Increase your productivity and performance

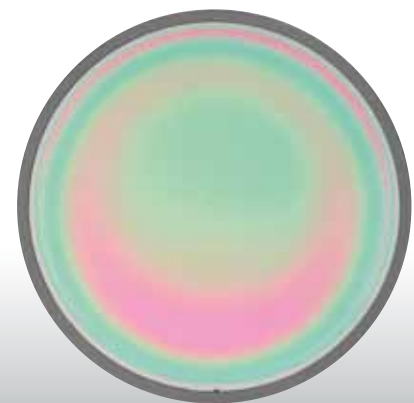
- ▶ Chosen by the best in the industry
- ▶ Highest throughput
- ▶ Lowest Cost of Ownership
- ▶ Highest yield performance
- ▶ 1st fully automated MOCVD platform with Cl_2 in-situ cleaning
- ▶ Cassette to cassette option to enable Si-style mass manufacturing

AIX G5+ characteristics

- ▶ Unique axis symmetric wafer performance like Si single wafer reactor
 - Wafer bow
 - Thickness, composition, concentration
 - Device yield
- ▶ Warm ceiling results in lowest heat flux through wafer
 - Smallest wafer bow by vertical temperature gradient
 - Enabling standard Si wafer thickness
- ▶ Customized temperature optimization by recess shaping

Process and Transfer Module

200 mm GaN on Si HEMT results
thickness uniformity 0.7 % standard deviation with 2 mm EE.



200 mm / 8 inch

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